BRF4N65
Rev.H Aug.-2023

蓝箭电子
BLUE ROCKET ELECTRONICS
DATA SHEET

/ Descriptions

TO-220F N MOS N-CHANNEL MOSFET in a TO-220F Plastic Package.

/ Features

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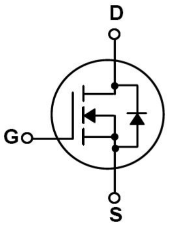
Low gate charge, low crss, fast switching.

/ Applications

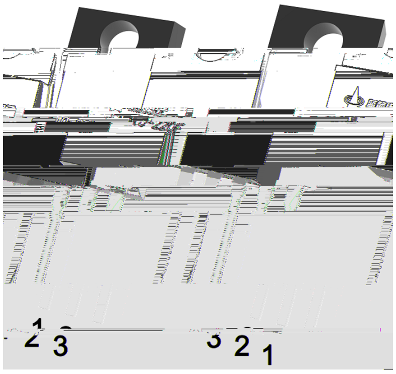
DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

/ Equivalent Circuit



/ Pinning



PIN1 G	PIN 2 D	PIN 3 S

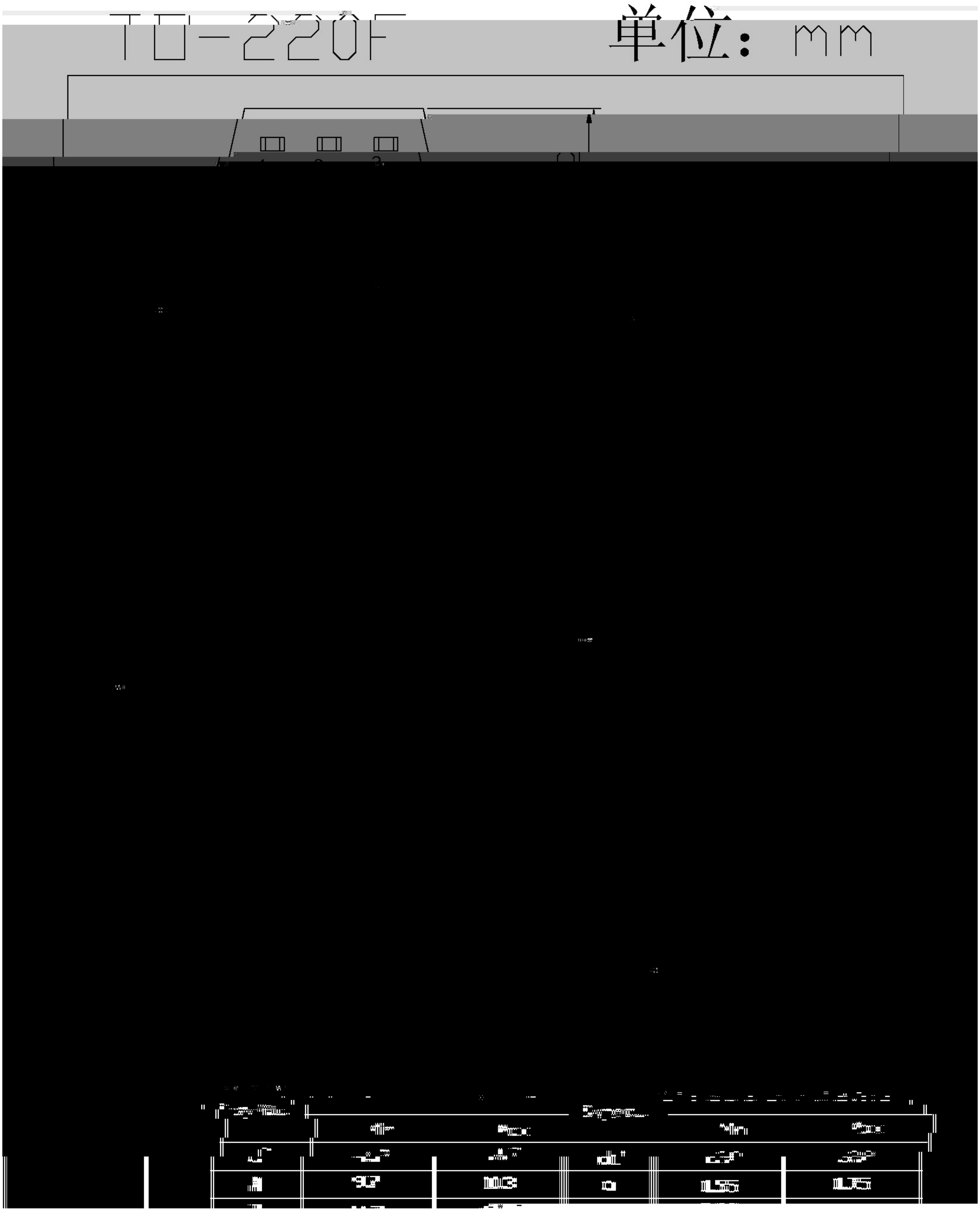
/ Marking

See Marking Instructions.

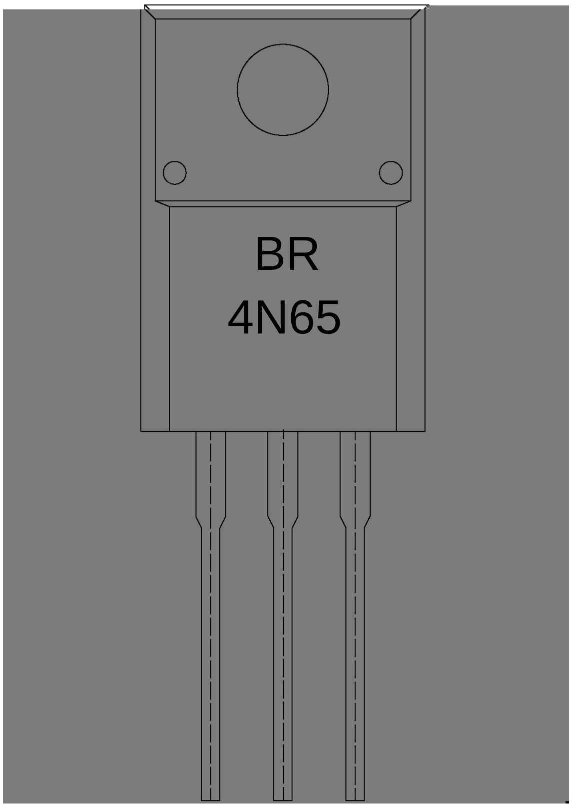
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	650	V
Drain Current	I_D(Tc=25)	4.0	A
Drain Current	I_D(Tc=100)	2.5	A
Drain Current - Pulsed	I_{DM}	16	A
Gate-Source Voltage	V_{GS}	±30	V
Single Pulsed Avalanche Energy	E_{AS}	240	mJ
Repetitive Avalanche Energy	E_{AR}	10	mJ
Avalanche Current	I_{AR}	4.0	A
Power Dissipation	P_D(Tc=25)	33	W
Operating and Storage Temperature Range	T_J,T_{STG}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250				

/ Package Dimensions



/ Marking Instructions



BR

4N65

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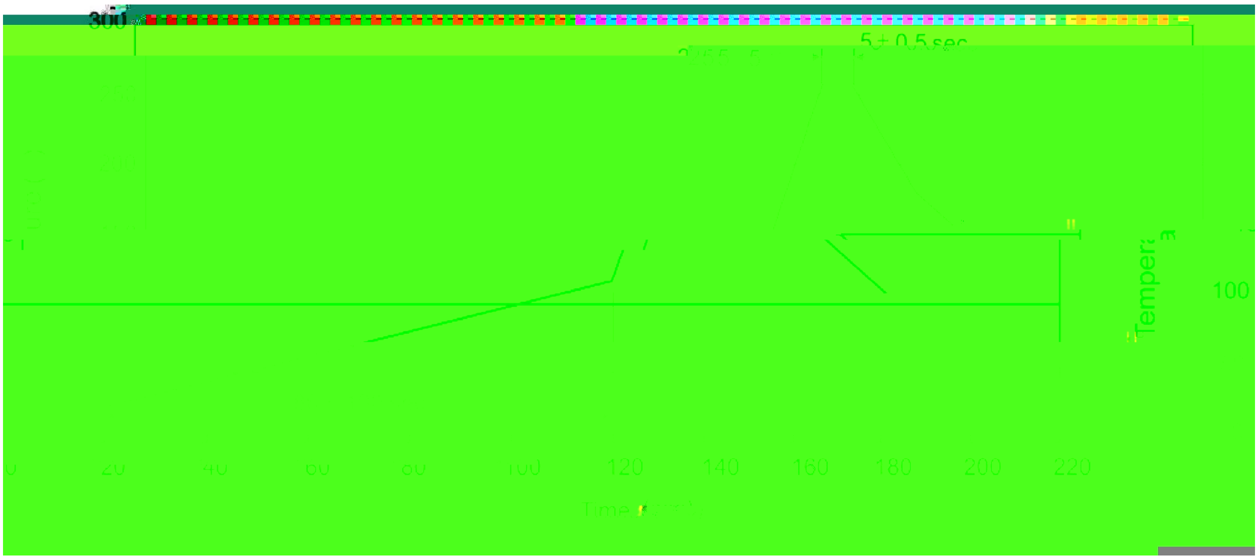
Note:

BR: Company Code

4N65: Product Type

****: Lot No. Code, code change with Lot No

( ) / Temperature Profile for Dip Soldering(Pb-Free)



	Note:
1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 255±5 5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5	10±1 sec.	Temp.:270±5	Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units	Diment.01603bd₮12